

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSIII)

# 2SJ681

Relay Drive, DC-DC Converter and Motor Drive Applications

- 4-V gate drive
- Low drain-source ON resistance:  $R_{DS(ON)} = 0.12 \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 5.0 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = -100 \mu\text{A}$  (max) ( $V_{DS} = -60 \text{ V}$ )
- Enhancement mode:  $V_{th} = -0.8$  to  $-2.0 \text{ V}$   
( $V_{DS} = -10 \text{ V}$ ,  $I_D = -1 \text{ mA}$ )

### Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	-60	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		$V_{DGR}$	-60	V
Gate-source voltage		$V_{GSS}$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	-5	A
	Pulse(Note 1)	$I_{DP}$	-20	A
Drain power dissipation		$P_D$	20	W
Single pulse avalanche energy (Note 2)		$E_{AS}$	40.5	mJ
Avalanche current		$I_{AR}$	-5	A
Repetitive avalanche energy (Note 3)		$E_{AR}$	2	mJ
Channel temperature		$T_{ch}$	150	°C
Storage temperature range		$T_{stg}$	-55~150	°C

### Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	6.25	°C / W
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	125	°C / W

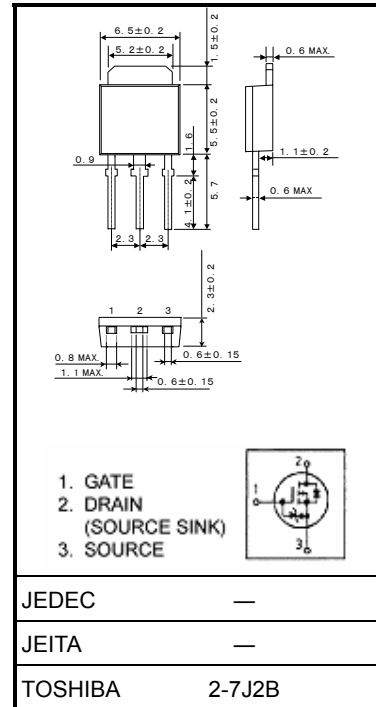
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = -25 \text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 2.2 \text{ mH}$ ,  
 $R_G = 25 \Omega$ ,  $I_{AR} = -5 \text{ A}$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.  
Please handle with caution.

Unit: mm



Weight: 0.36 g (typ.)

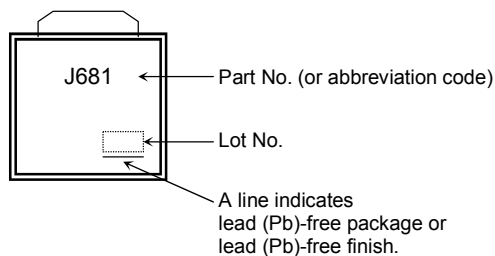
## Electrical Characteristics (Ta = 25°C)

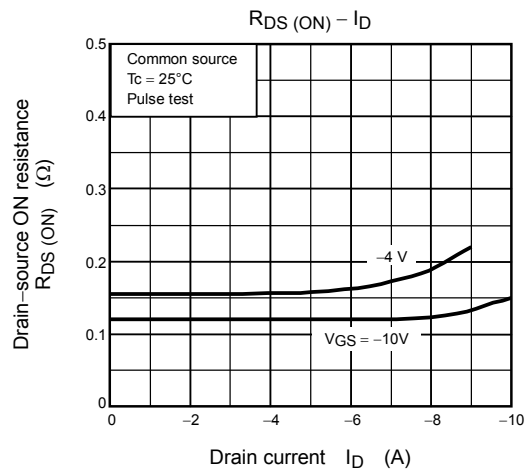
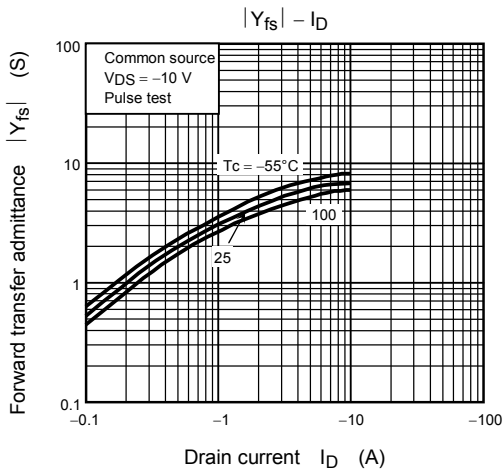
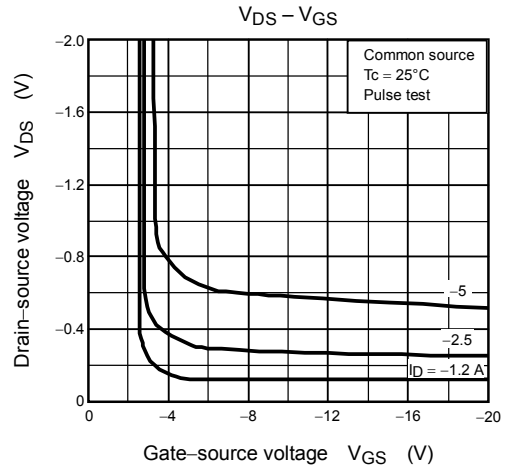
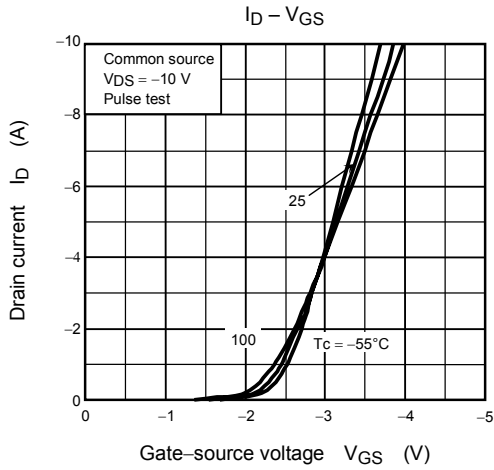
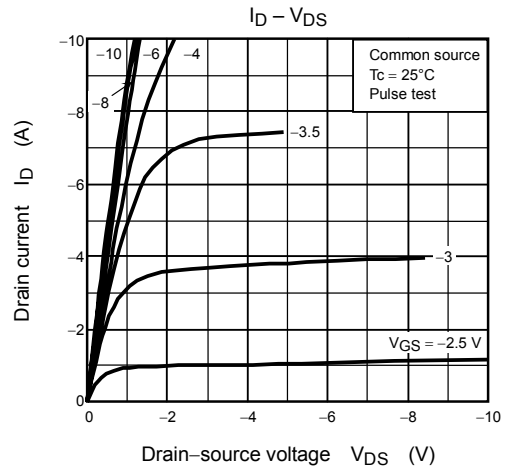
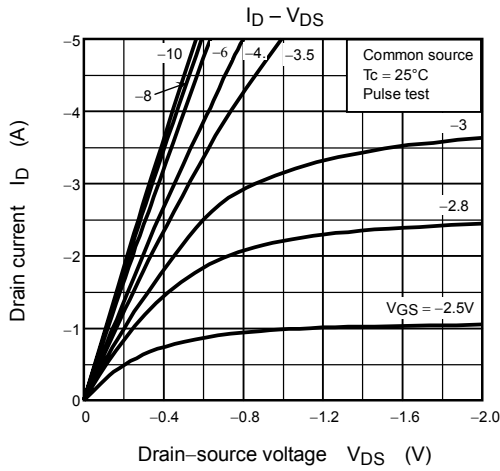
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-off current		$I_{DSS}$	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	-100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-60	—	—	V
		$V_{(BR)DSX}$	$I_D = -10 \text{ mA}, V_{GS} = 20 \text{ V}$	-35	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-0.8	—	-2.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = -4 \text{ V}, I_D = -2.5 \text{ A}$	—	0.16	0.25	$\Omega$
			$V_{GS} = -10 \text{ V}, I_D = -2.5 \text{ A}$	—	0.12	0.17	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = -10 \text{ V}, I_D = -2.5 \text{ A}$	2.5	5.0	—	S
Input capacitance		$C_{iss}$	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	700	—	pF
Reverse transfer capacitance		$C_{rss}$		—	60	—	
Output capacitance		$C_{oss}$		—	90	—	
Switching time	Rise time	$t_r$		—	14	—	ns
	Turn-on time	$t_{on}$		—	24	—	
	Fall time	$t_f$		—	14	—	
	Turn-off time	$t_{off}$		Duty $\leq 1\%$ , $t_w = 10 \mu\text{s}$	—	95	
Total gate charge (Gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx -48 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -5 \text{ A}$	—	15	—	nC
Gate-source charge		$Q_{gs}$		—	11	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	4	—	

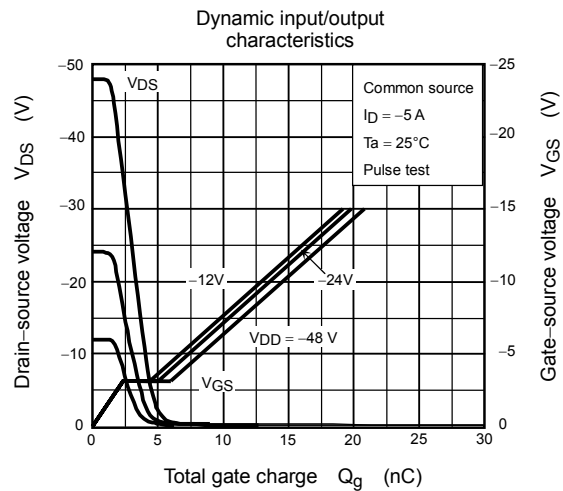
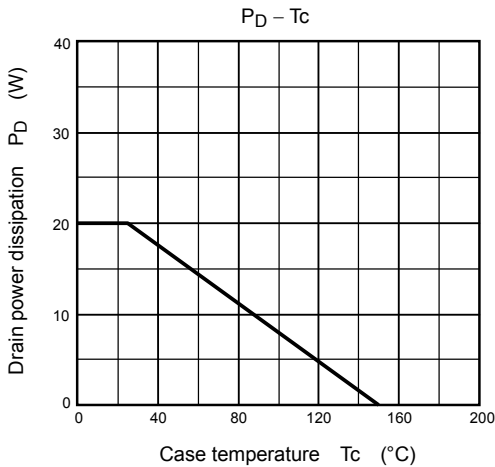
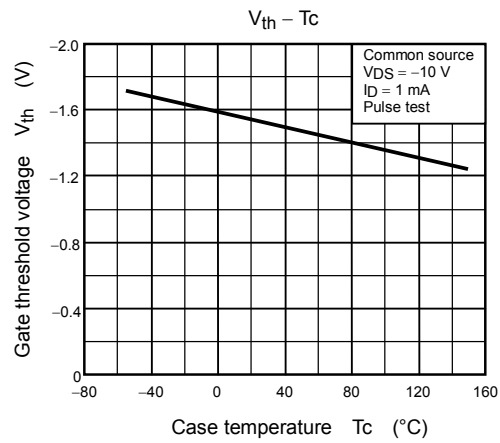
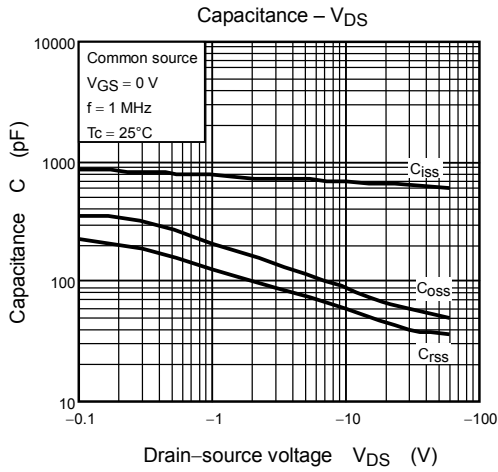
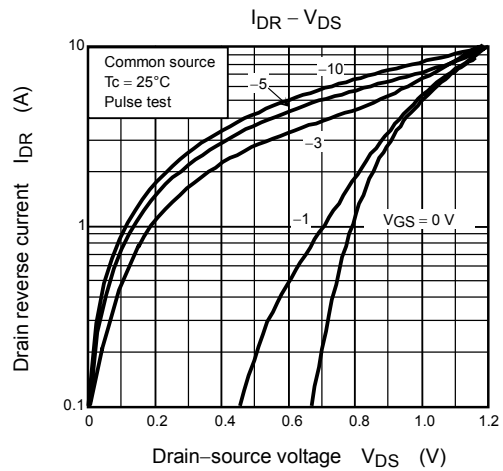
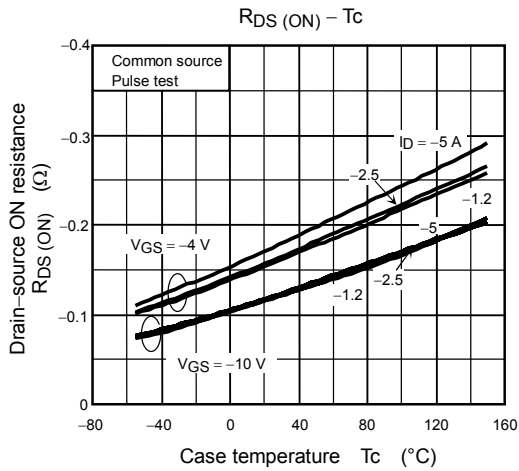
## Source-Drain Ratings and Characteristics (Ta = 25°C)

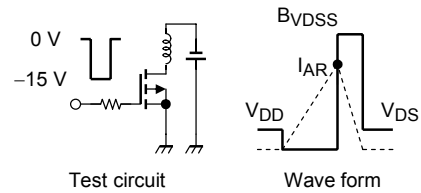
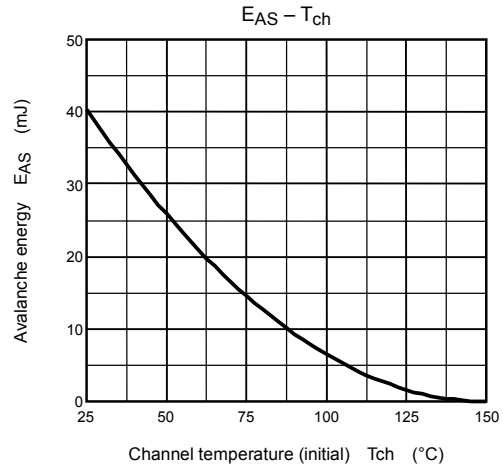
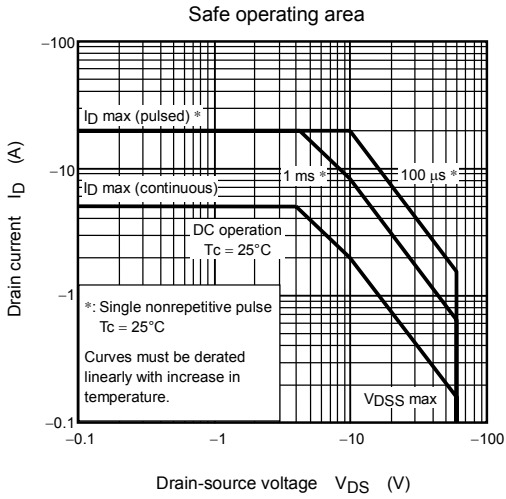
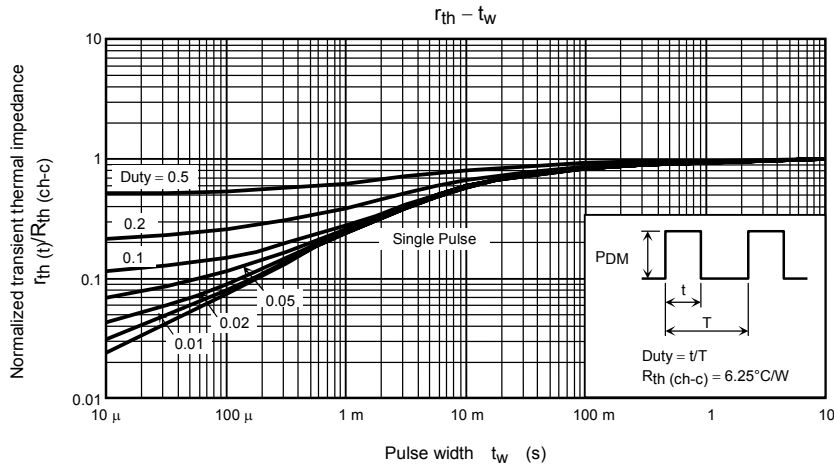
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	-5	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	-20	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = -5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	1.7	V
Reverse recovery time	$t_{rr}$	$I_{DR} = -5 \text{ A}, V_{GS} = 0 \text{ V}$	—	40	—	ns
Reverse recovery charge	$Q_{rr}$	$dI_{DR} / dt = 50 \text{ A} / \mu\text{S}$	—	32	—	nC

## Marking









$R_G = 25 \Omega$   
 $V_{DD} = -25 \text{ V}, L = 2.2 \text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I_{AR}^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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